Im aging Spin Reorientation Transitions in Consecutive Atom ic Co layers on Ru (0001)

Farid ElGabaly, Silvia Gallego, Carmen Muroz, Laszlo Szunyogh, Peter Weinberger, Christof Klein, Andreas K. Schmid, Kevin F. McCarty, and Juan de la Figuera

1Dpto. de Fisica de la Materia Condensada and Centro de Microanalisis de Materiales,
Universidad Autonoma de Madrid, Madrid 28049, Spain

2Instituto de Ciencia de Materiales de Madrid, CSIC, Madrid 28049, Spain

3Department of Theoretical Physics and Center for Applied Mathematics and Computational Physics,
Budapest University of Technology and Economics, Budafoki ut 8, H-1521 Budapest, Hungary

4Center for Computational Materials Science, Vienna University of Technology, Gumpendorferstr. 1a, A-1060 Vienna, Austria

5Lawrence Berkeley National Laboratories, Berkeley, California 94720, USA

6 Sandia National Laboratories, Livermore, California 94550, USA

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By means of spin-polarized low-energy electron microscopy (SPLEEM), we show that the magnetic easy-axis of one to three atom ic-layer thick cobalt lms on Ru (0001) changes its orientation twice during deposition: one-monolayer and three-monolayer thick lms are magnetized in-plane, while two-monolayer lms are magnetized out-of-plane. The Curie temperatures of lms thicker than one monolayer are well above room temperature. Fully-relativistic calculations based on the Screened Korringa-Kohn-Rostoker (SKKR) method demonstrate that only for two-monolayer cobalt lms the interplay between strain, surface and interface elects leads to perpendicular magnetization.

K eyw ords: m agnetism, m agnetic m aterials, m agnetic anisotropy, thin lm s, spin polarized low energy electron m icroscopy, R u, C o

Applications of ferrom agnetic Ims depend on understanding and controlling the direction of the easy-axis of m agnetization. In particular, m agnetization perpendicular to the Im plane [1, 2, 3, 4] holds prom ise for novel inform ation-processing technologies [5]. Two important features of ultra-thin Ims underlie this technological achievem ent: the high Curie temperature of transition metal Ims and the ability to control their microstructure. To provide deeper understanding, we study thin-Im magnetism in a system whose components do not interm ix, Co and Ru. Previous work [6, 7] has shown that the easy axis of magnetization in Co/Ru multilayers changes from perpendicular at low Cothickness to inplane for lm sthickerthan 7 M L [8]. Because the Co lm s did not grow layer-by-layer[9, 10], the lms contained islands of varying thickness. Under these conditions, determ ining precisely how the magnetization changes as a function of Im thickness is quite problem atic.

Here we deposit Co Ims under conditions of perfect layer-by-layer growth. Then we use in-situ spin-polarized low-energy electron microscopy (SPLEEM) [11, 12, 13] to locally determine the magnetization orientation of one-, two-, and three-monolayer thick Co Ims. We observe that the easy axis of magnetization changes after the completion of each atomic layer. By combining structural, morphological and microscopic magnetic measurements with fully relativistic ab-initio calculations based on the screened Korringa-Kohn-Rostoker (SKKR)[14] method, we explain the origin of the magnetization changes. Our results highlight that the magnetic anisotropy of ultra-thin Ims is not simply explained by strain or interface e ects alone, but often by a combination of both e ects.

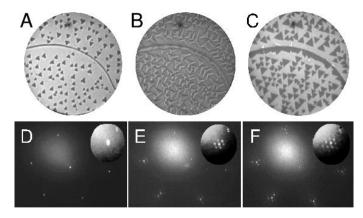


FIG. 1: LEEM images and direction patterns of a Co Imgrowing on Ru (0001). (a)—(c): LEEM images show the morphology of the growing Im. Field of view is 10 m, electron energy is 5 eV, and grow them perature is 460 K. One single, curved Ru step crosses the images. (a) 1 M L Co islands (dark) on Ru (light gray background). (b) 2 M L islands (light gray) on a complete 1 M L Im (dark gray). (c) 3 M L islands (dark gray) on a nearly complete 2 M L Im (light gray). (d)—(f) LEED patterns (70 eV) obtained from selected Imareas of uniform thickness. Insets show magnied views of the specular beam. (d) 1 M L, (e) 2 M L and (f) 3 M L of Co/Ru (0001).

The lms are grown in two dierent ultra-high vacuum low-energy electron microscopes (LEEM and SPLEEM)[11] by physical vapor deposition from calibrated dosers at rates of 0.3 M L/m in. Details of the substrate-cleaning procedure as well as the experimental system are given elsewhere[16]. Perfect layer-by-layer C o grow th occurs up to at least 7 M L when the Ru substrate has a low density of atom ic steps (Fig.1a-c). Because sub-

strate steps enable a kinetic pathway to the nucleation of new Im layers, three-dim ensional growth [8, 9] occurs after the stem on olayer if substrate steps are present at even moderate density [17]. The lm structure is determ ined by selected-area low-energy electron di raction (LEED), ie., the diraction patterns were acquired with diracted electrons coming from areas of the lm with uniform thickness. One-monolayer Imsalways present a 1 1 LEED pattern indicating pseudom orphic growth, that is, the lm has the same in-plane lattice parameter as the substrate (Fig. 1d). Since the in-plane lattice param eter of bulk Co is 7.9% sm aller than that of Ru, both m easured within the hexagonal-close-packed (hqp) basal plane, the rst m onolayer of Co is under pronounced tensile strain. A nalysis of the intensity versus energy curves of the specular and integer di raction spots establishes that the Co Im continues the hop stacking [18] of the substrate, with a Co-Ru interplanar separation estimated to be contracted 6% relative to the Ru-Ru interplanar spacing. For lms thicker than 1 ML, satellite spots appear around the bulk di raction beam s (Fig. 1e-f), i.e., the thicker Ims are no longer pseudom orphic. From the di raction patterns, we estimate that the in-plane spacing of 2 M L and 3 M L Co Imsis 5 1% less than the Ru spacing, leaving the Im strained only by 3% relative to the bulk-Co value. At intermediate coverages between 1 M L and 2 M L, the 1 M L areas are still pseudom orphic, as detected by dark-eld im aging [16], while 2 M L islands are relaxed and 3 M L Ims grow mainly in a face-centered-cubic structure.

To characterize the easy axis of magnetization, we em ploy SPLEEM [13]. With this technique the magnetization can be mapped onto three orthogonal directions [19]: the absence of contrast in the images (gray) indicates no m agnetization component along the selected direction; bright and dark areas indicate a component of the magnetization along or opposed to the illum inating beam polarization, respectively. In Fig. 2 we show LEEM and SPLEEM images of a lm that consists of a complete monolayer of Co plus some second layer islands (Fig. 2a), both in the middle of the substrate terraces and at the bottom of the ruthenium substrate steps. The SPLEEM images show the spatially resolved component of the magnetization in three orthogonal directions: two in-plane (Fig. 2b-c) and one out-of-plane (Fig. 2d). In one-m on olayer areas the m agnetization is oriented in the plane of the lm, while for two layer islands the magnetization is out-of-plane. For a complete 2 M L lm with additional 3 M L islands (Fig. 3), the magnetization of the 2 M L areas is out-of-plane. In contrast, 3 M L thick islands and thicker Ims (not shown) are magnetized in-plane. To sum marize, two magnetization easyaxis reorientation transitions are found in three consecutive atom ic layers: at the crossover between 1 and 2 M L, and between 2 and 3 M L. This behavior has also been con med in lmsdevoid of islands. We do not not inter-

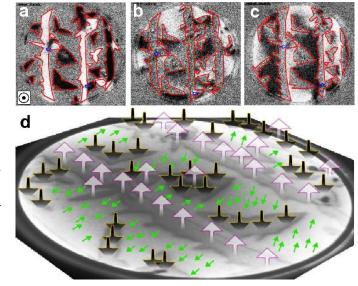


FIG. 2: (color) Im ages of topography and magnetization of one region of a 1.5 M L C o/R u (0001) Im. Im ages were taken at 110 K.Field of view is 2.8 m and electron energy is 7 eV. (a)—(c) SPLEEM images with electron-polarization oriented: (a) out-of-plane; (b) in-plane and 13 o a compact-direction; (c) in-plane and 103 o a compact-direction. 2 M L islands are framed in red (two small 3 M L islands are framed in blue). (d) LEEM image of the surface with the deduced magnetization direction indicated by arrows (black and white arrows mean out-of-plane magnetization, green arrows mean in-plane magnetization). Dark gray indicates 2 M L islands, light gray 1 M L im

m ediate easy-axis orientations (i.e., in between in-plane and out-of-plane), such as observed for Co lms on other substrates [20, 21]. The Curie temperature of the lms changes dram atically from the rst layer to the second. The rst layer has a Curie temperature close to 170 K, as detected by the loss of magnetic contrast in the 1 M L areas. The Curie temperature of the 2 M L islands, which are magnetized out-of-plane, is well above room temperature, about 470 K. Thicker lms exhibit Curie temperatures above 470 K. Iron lms on W (110) [22, 23] also present a double spin reorientation transition, but with a Curie temperature well below room temperature for out-of-plane magnetization [24]. In this particular system, strain did not drive the reorientation transitions [24, 25].

The anisotropy energy that governs the orientation of the easy-axis of magnetization is the result of a delicate balance between dierent contributions. In thin Ims the dominating term is offen the dipolar or shape anisotropy. This contribution, which results from the long-range magnetic dipole-dipole interactions, favors an in-plane orientation of the magnetization. However, other contributions such as the bulk, interface and surface magnetocrystalline anisotropy energies, as well as magneto-elastic term s[15, 26], can compete with the dipolar anisotropy energy and can favor out-of-plane magnetization. To un-

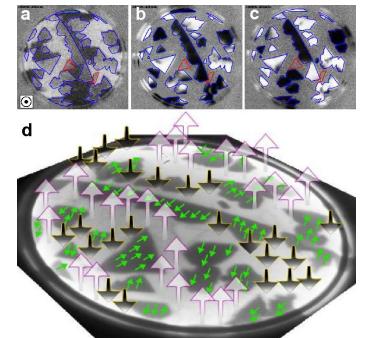


FIG. 3: (color) Im ages of topography and m agnetization of one region of a  $2.5\,\mathrm{M}\,\mathrm{L}$  C o/R u (0001) Im. Im ages were taken at room temperature. Field of view is  $2.8\,\mathrm{m}$  and electron energy is 7 eV. (a)-(c) SPLEEM images with electron-polarization oriented: (a) out-of-plane; (b) in-plane and 13 o a compact-direction; (c) in-plane and 103 o a compact-direction. 3 M L islands are framed in blue. Two vacancy-islands in the  $2\,\mathrm{M}\,\mathrm{L}$  area, where Co is  $1\,\mathrm{M}\,\mathrm{L}$  thick, are framed in red. (d) LEEM image of the surface with the deduced magnetization direction indicated by arrows (black and white arrows mean out-of-plane magnetization, green arrows mean in-plane magnetization). Dark gray indicates  $3\,\mathrm{M}\,\mathrm{L}$  islands, light gray  $2\,\mathrm{M}\,\mathrm{L}$  Im.

derstand the e ects that give rise to the observed changes in the orientation of the C o m agnetization, we perform ab-initio calculations in terms of the SKKR m ethod [14]. Changing the lattice parameters in the calculations allows us to determ ine how strain in uences the magnetic anisotropy. The magnetic anisotropy energy (MAE) is calculated as the dierence of the total energy for inplane and out-of-plane magnetization. A positive MAE corresponds to out-of-plane magnetization. By employing the force theorem [27], the MAE is de ned as the sum of a band energy, E  $_{\rm b}$ , and a magnetic dipoledipole energy term, E  $_{\rm dd}$ . The band-energy term can be further resolved into contributions with respect to atom ic layers that enable us to de ne surface and interface anisotropies.

First, we calculate the anisotropy of the pseudom orphic one-monolayer Co  $\,$  lm s, taking into account contractions of the Co-Ru interlayer distance (d). As sum-marized in Fig. 4a, the value of E  $_{\rm b}$  increases as the interplanar spacing decreases; however, due to the negative

E  $_{\rm dd}$ , the preferred orientation of the magnetization remains always in-plane. Interestingly, the change in MAE is not proportional to the strain and, therefore, simple magnetoelastic arguments do not apply. Furthermore, we also tested the e ect of contracting the in-plane lattice parameter of substrate and lm. In that case, the MAE does not change signicantly (result not shown in the gure). We conclude that the magnetization of the monolayer remains in-plane regardless of strain.

For two-monolayer and thicker Ims, the in-plane separation of the Co atoms is contracted by 5% with respect to the Ru structure, leading to a 20x20 coincidence lattice. We model the in-plane relaxation by contracting the supporting Ru substrate together with the Co lm. Under this assumption, taking the same contraction for the Co-Co and Co-Ru interlayer spacing d from 0 to 7% relative to the substrate interlayer distance leads to a positive value of E b (Fig.4b) that, however, does not compensate the negative  $\,\,{\rm E}_{\rm dd}\,.$  For the bilayer, the observed positive sign of the MAE occurs when dierent values for the Co-Co and Co-Ru interlayer distances are considered. In order to estimate the preferred relaxation of the interlayer distances we assume that atoms try to maintain the nearest-neighbors (NN) distances of their bulk materials, with Co-Ru distances being an average of the preferred Co-Co and Ru-Ru interlayer distances. This leads to contractions of 7% for the Co-Co interlayer distances and a nearly unrelaxed Co-Ru spacing. As shown in Fig. 4b (leftmost data points), such a lattice distortion considerably increases E b resulting in a total positive MAE.A positive MAE is also obtained for an ideal Ru lattice with Co interlayer distances contracted by more than 4% (not shown). In 3 M L thick lms, non-uniform contractions of the Co layers lead also to an enhancem ent of the positive E b (Fig.4c). Nevertheless, the decrease in the  $\, {\rm E}_{\rm dd} \,$  term associated with thicker Im s drives the magnetization in-plane. A sum mary of our calculations of the MAE for the Co lms of dierent thickness, each at the most likely geometry, is shown in Fig. 4d. As a function of thickness the MAE changes sign twice, as observed experim entally.

Our calculations show that the double spin-reorientation transition is the result of a complicated interplay of structural and interface/surface electronic e ects. All contributions to E  $_{\rm b}$  are strongly in uenced by structural modi cations. For 2 M L thick  $\,$  lm s with the same Co-Co and Co-Ru interlayer separation, the dominant term is E  $_{\rm b}$  related to the interface Co. How-ever, when Co-Co and Co-Ru separations are allowed to be dierent, the contribution of the surface Co layer is remarkably enhanced resulting in a positive value of the MAE (out-of-plane magnetization).

In conclusion, we deposited Im s of Co onto Ru (0001) in the thickness range of up to 3 atom ic monolayers and nd that the Curie temperature is well above room temperature, provided the thickness is more than a single

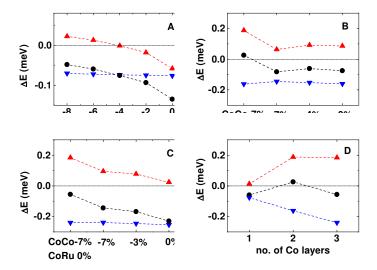


FIG. 4: (color) Calculated magnetic anisotropy energies of the dierent Co  $\,$ lm s on Ru. (a)-(c) D ependence of the calculated MAE on the interlayer distance referred to the substrate interlayer spacing. MAE (black circle) and its components, E  $_{\rm b}$  (red up-triangle) and E  $_{\rm dd}$  (blue down-triangle) for: (a) a pseudom orphic 1 M L C o/R u (0001)  $\,$ lm under dierent contractions of the Co-R u interlayer distance; in-plane strained (b) 2 M L C o/R u (0001) and (c) 3 M L C o/R u (0001)  $\,$ lm s w ith either the same or dierent (data points labelled by C oC o-7% and C oR u 0%) C o-C o and C o-R u interlayer separations. (d) MAE and its components in the most realistic geometry for the 1, 2 and 3 M L C o  $\,$ lm s on R u (0001), displaying the double reorientation transition.

atom ic monolayer. We observe two sharp reorientation transitions of the magnetization: 1 ML as well as 3 ML or thicker Co lms have an in-plane easy axis, while only 2 ML thick lms are magnetized in the out-of plane direction. The rst transition is associated with a structural transformation from laterally strained, pseudomorphic 1 ML thick lms to relaxed 2 ML thick lms. Our rst principles calculations show that the in-plane easy-axis of one- and three-monolayer lms is stable with respect to variations of the strain conditions. Only for two-monolayer lms, the combination of strain with additional interface and surface e ects drives the magnetic easy-axis into the out-of-plane direction.

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- Electronic address: faridelgabaly@uam.es; http://hobbes.fmc.uam.es/loma
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